

## UHF-Band Avionics Transistor

The high power pulsed avionics transistor part number IB0607S100 is designed for UHF-Band avionics systems operating at 653 to 687 MHz. While operating in class C mode under 20us pulse conditions at  $V_{CC}=50V$ , this common base device supplies a minimum of 120 watts of peak pulse power. It utilizes a low loss internal input impedance matching structure to yield maximum device gain and to ease the implementation of external matching circuitry. The new generation bipolar transistor geometry utilizes a gold metallization system to achieve maximum reliability. Emitter ballast resistance is incorporated on the active cell for optimum thermal distribution and maximum reliability. All devices are 100% screened for large signal RF parameters.

### Silicon Bipolar

- Ultra-high  $f_T$

### Class C Operation

- High Efficiency

### Common Base Configuration

- Single Power Supply

### Gold Metal

- Maximum Reliability

### Emitter Ballasting

- Optimum Thermal Distribution

### Internal Impedance Matching

- Ease of Use
- Ultra-low Loss Design

### BeO Package

- Unmatched Thermal Reliability

### RF Test Fixture

- Broadband
- Matched to 50Ω
- Long-term Correlation
- 100% Device RF Screening
- No External Tuning Allowed
- Micro-strip structure on soft pc board with dielectric constant 10.2

PRELIMINARY DATA

PRELIMINARY DATA

PRELIMINARY DATA

Device	Freq (MHz)	$V_{CC}$ (V)	$P_{IN}$ (W)	IRL (dB)	$P_{OUT}$ (W)	$G_P$ (dB)	$I_c$ (A)	$\eta_c$ (%)	Droop (dB)
50028200-1	653	50	5.85	18	120	13.12	3.39	70.8	0.03
	670	50	5.18	18	120	13.65	3.45	69.7	0.02
	687	50	5.58	18	120	13.33	3.89	61.8	0.03

Pulse Format : PW=20us, DF=2%

**MAXIMUM RATINGS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Collector-Emitter Voltage	$V_{CES}$	--	75	V	--
BD	Emitter-Base Voltage	$V_{EBO}$	--	2	V	--
BD	Storage Temperature Range	$T_{STG}$	-60	+150	°C	--
BD	Operating Junction Temperature Range	$T_J$	-60	+200	°C	--
Note	Screen 'BD' = parameter qualified By Design.					

**THERMAL CHARACTERISTICS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Thermal Resistance	$R_{TH(JC)}$	--	0.12	°C/W	$P_{OUT}=120W, P_{IN}=10W, N_C=40\%, V_{CC}=50V, PW=20\mu s, DF=2\%, T_F=30\pm 5^\circ C$
BD	MTTF	MTTF	4.89E13	--	Hrs	$P_{OUT}=120W, P_{IN}=10W, N_C=40\%, V_{CC}=50V, PW=20\mu s, DF=2\%, T_F=30\pm 5^\circ C$
Note	Screen 'BD' = parameter qualified By Design.					

**PROCESSING SPECIFICATIONS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	DC Wafer Probe	--	--	--	--	Per Integra specification.
Q1	Wafer DC and RF Qualification	--	--	--	--	Per Integra specification.
LM	Wire Bond Strength	--	--	--	--	Line monitor per Integra specification.
100%	Pre-cap visual inspection	--	--	--	--	Per Integra specification
100%	Gross leak test	--	--	--	--	MIL-STD-750D, Method 1071, Test Condition C
Note	Screen 'Q1' = parameter is qualified by assembly and test of 3 pieces minimum per wafer.					
Note	Screen 'LM' = parameter is qualified by assembly line monitor.					

**DC ELECTRICAL CHARACTERISTICS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Collector-Emitter Breakdown Voltage	$BV_{CES}$	75	--	V	$I_C = 40mA, V_{BE} = 0V, T_F = 25\pm 5^\circ C$ .
100%	Zero Base Voltage Collector Leakage Current	$I_{CES}$	--	2.0	mA	$V_{CE} = 50V, V_{BE} = 0V, T_F = 25\pm 5^\circ C$ .
100%	DC Current Gain	$H_{FE}$	20	100	--	$V_{CE} = 5V, I_C = 100mA, T_F = 25\pm 5^\circ C$ .

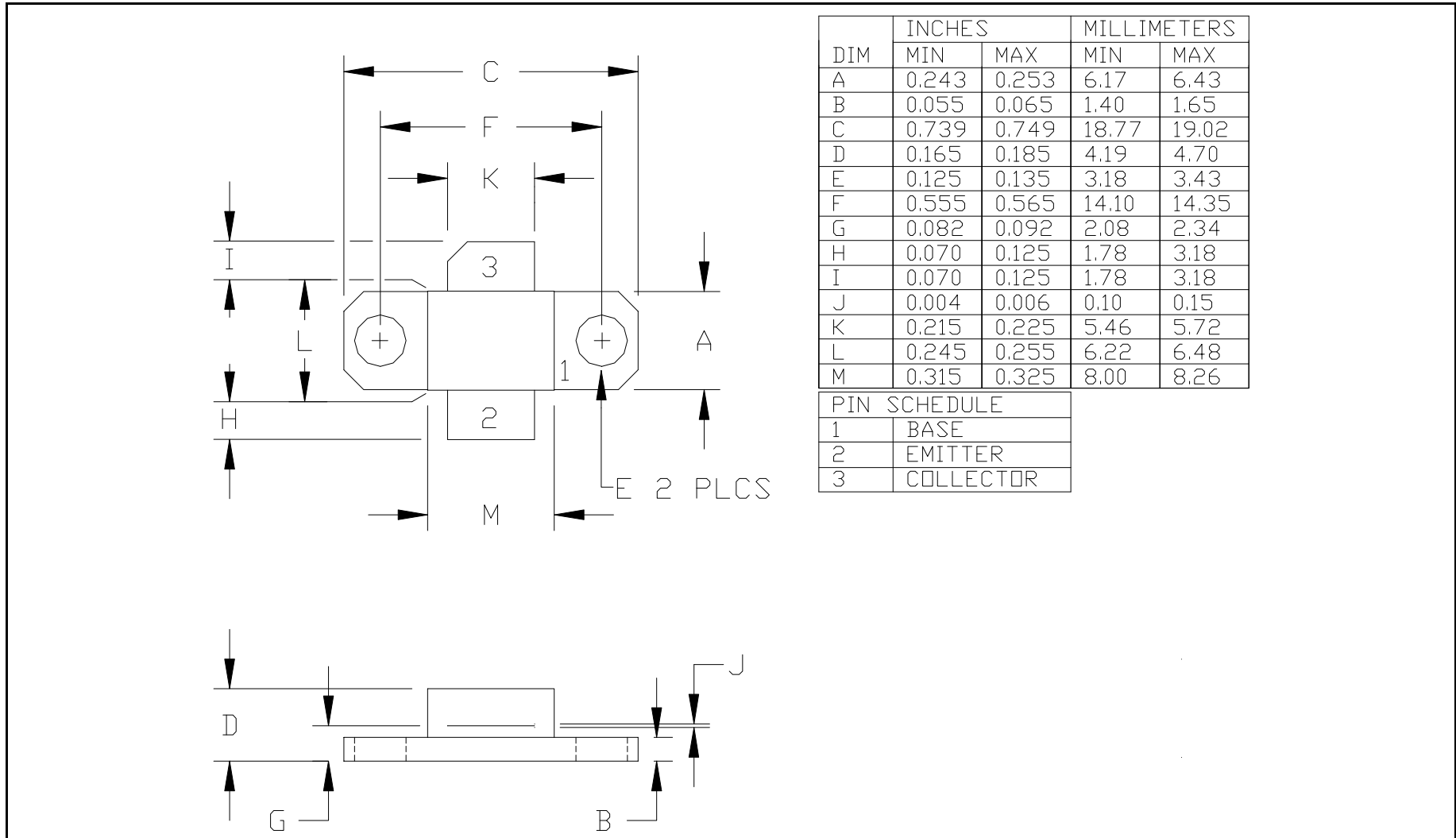
## RF ELECTRICAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Input Return Loss	IRL	8	--	dB	$V_{CC}=50V$ , $P_{OUT}=120W$ , Pulse = Note 2, $T_F=30\pm5^\circ C$ , F=F1, F2, F3
100%	Power Gain	$G_P$	11	14	dB	$V_{CC}=50V$ , $P_{OUT}=120W$ , Pulse = Note 2, $T_F=30\pm5^\circ C$ , F=F1, F2, F3
100%	Collector Efficiency ( $P_O/I_C/V_{CC}$ )	$N_C$	40	--	%	$V_{CC}=50V$ , $P_{OUT}=120W$ , Pulse = Note 2, $T_F=30\pm5^\circ C$ , F=F1, F2, F3
100%	Pulse Amplitude Droop	D	--	0.5	dB	$V_{CC}=50V$ , $P_{OUT}=120W$ , Pulse = Note 2, $T_F=30\pm5^\circ C$ , F=F1, F2, F3
100%	Stability into 1.5:1 VSWR	VSWR-S	--	2:1	--	$V_{CC}=50V$ , $P_{OUT}=120W$ , Pulse = Note 2, $T_F=30\pm5^\circ C$ , F=F1, F2, F3 Rotate 2:1 output VSWR through 360° phase. No oscillatory or pulse break-up characteristics allowed on detected output pulse.
100%	Load Mismatch Tolerance	LMT		3:1	--	$V_{CC}=50V$ , $P_{OUT}=120W$ , Pulse = Note 2, $T_F=30\pm5^\circ C$ , F=F1, F2, F3 Rotate 3:1 output VSWR through 360° phase. Survival.
BD	Maximum Input Overdrive	MIO	--	1.0	dB	$V_{CC}=50V$ , $P_{OUT}=120W$ , Pulse = Note 2, $T_F=30\pm5^\circ C$ , F=F1, F2, F3
BD	Pulse Risetime	RT	--	100	ns	$V_{CC}=50V$ , $P_{OUT}=120W$ , Pulse = Note 2, $T_F=30\pm5^\circ C$ , F=F1, F2, F3 Measure between 10% and 90% detected power points.
Note 1	F1 = 653MHz, F2 = 670MHz, F3 = 687MHz					
Note 2	Pulse Format : PW=20us, DF=2%					
Note 3	$T_F$ = Device flange temperature.					
Note 4	Screen 'BD' = parameter qualified By Design.					
Note 5	Continuous operation at $V_{CC}=55V$ is allowed only for PW=3us and DF<0.5%					

## RF TEST FIXTURE IMPEDANCE CHARACTERISTICS

Frequency (MHz)	$Z_{IF}$ ( $\Omega$ )	$Z_{OF}$ ( $\Omega$ )
653	4.2-j2.2	2.5+j2.6
670	4.2-j1.6	2.6+j3.2
687	4.2-j1.1	2.7+j3.9
Impedance Definition		

**PACKAGE DIMENSIONAL OUTLINE DRAWING**



Part Number: **IB0607S100 (Preliminary)**

**Integra**  
TECHNOLOGIES, INC.

**RF TEST FIXTURE DRAWING**

SEE RF TEST FIXTURE CAD DRAWING

**DEFINITIONS**

<b>Data Sheet Status</b>	
Proposed Specification	This data sheet contains proposed specifications.
Preliminary Specification	This data sheet contains specifications based on preliminary measurements and data.
Product Specification	This data sheet contains final product specifications.
<b>Maximum Ratings</b>	
Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only and operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.	

**WARNING**

<b>Product and environmental safety - toxic materials</b>
This product contains beryllium oxide. The product is entirely safe provided that the BeO base is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with general or domestic waste.

**DISCLAIMER**

Integra Technologies Inc. reserves the right to make changes without further notice to any products herein. Integra Technologies Inc. makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Integra Technologies Inc. assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. Integra Technologies Inc. products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Integra Technologies Inc. customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Integra Technologies Inc. for any damages resulting from such improper use or sale.
--